

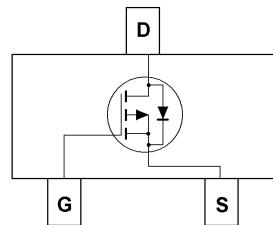
P-Channel Enhancement Mode MOSFET

Feature

- 20V/-3A, RDS(ON) = 120mΩ(MAX) @VGS = -4.5V.
RDS(ON) = 150mΩ(MAX) @VGS = -2.5V.
- Super High dense cell design for extremely low RDS(ON)
- Reliable and Rugged
- SOT-23 for Surface Mount Package



SOT-23



Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings

TA=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±10	V
Drain Current-Continuous	I _D	-3	A

Electrical Characteristics

TA=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	V _{GS} =0V, ID=-250μA	-20	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0V	-	-	-1	μA
Gate Body Leakage Current, Forward	IGSSF	V _{GS} =10V, V _{DS} =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V _{GS} =-10V, V _{DS} =0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , ID=-250μA	-0.4	-	-1.0	V
Static Drain-source	RDS(ON)	V _{GS} =-4.5V, ID =-3.0A	-	--	120	mΩ
On-Resistance		V _{GS} =-2.5V, ID =-2.0A	-	--	150	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	V _{GS} =0V, IS=-1.25A			-1.2	V

Typical Characteristics

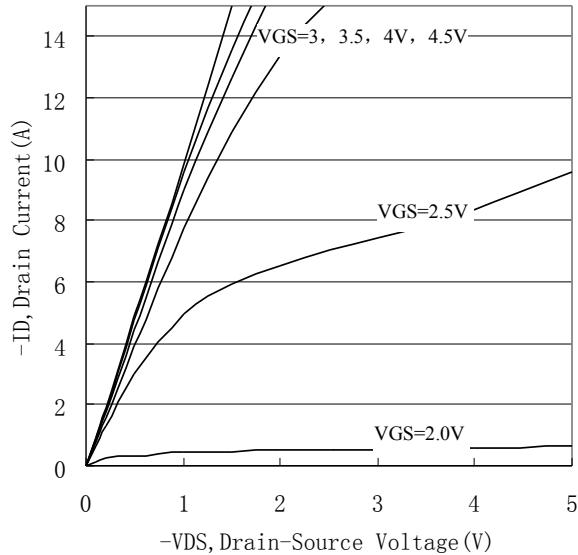


Figure 1. Output Characteristics

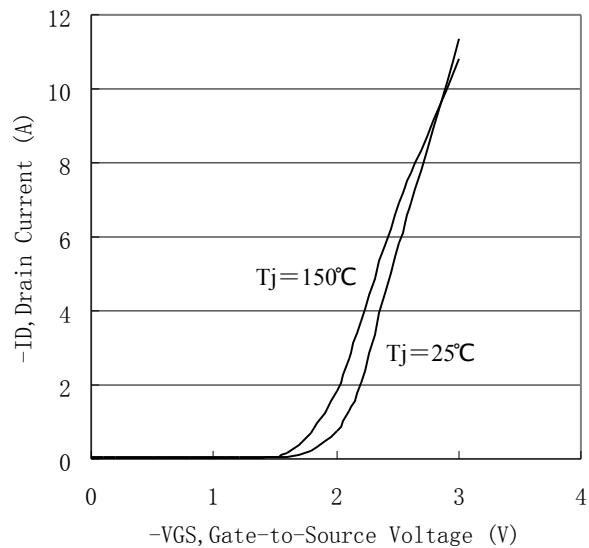


Figure 2. Transfer Characteristics

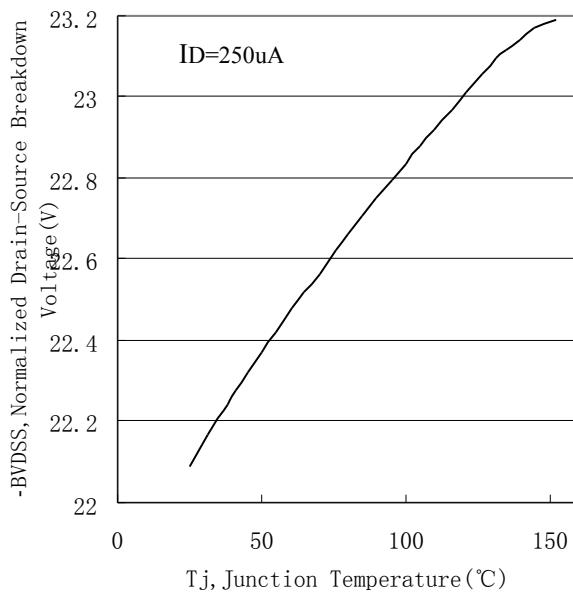


Figure 3. Breakdown Voltage Variation with Temperature

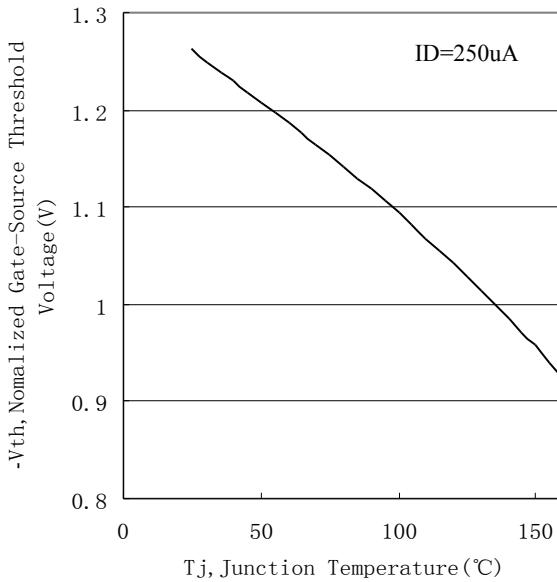


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

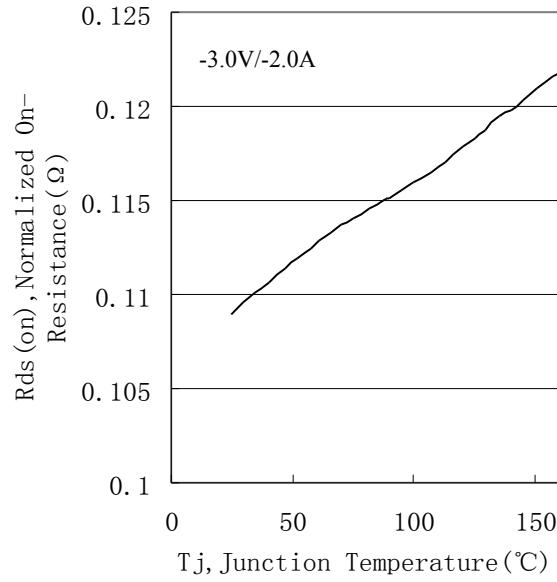


Figure 5. On-Resistance Variation with Temperature

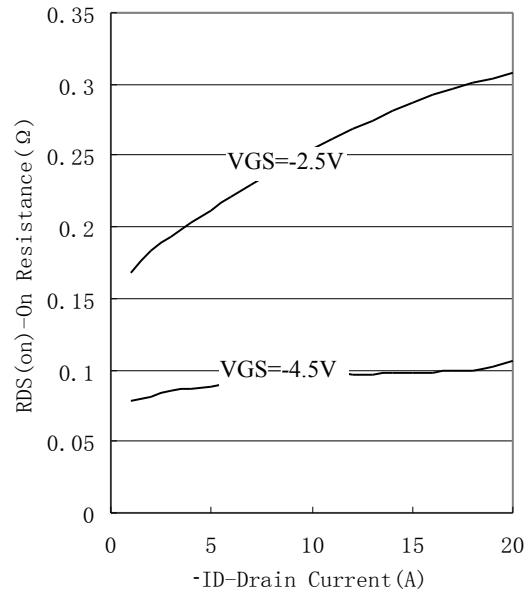


Figure 6. On-Resistance vs. Drain Current

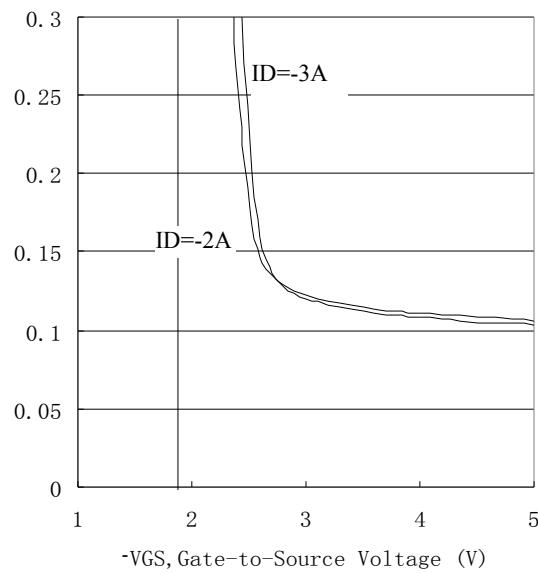


Figure 7. On-Resistance vs. Gate-to-Source Voltage

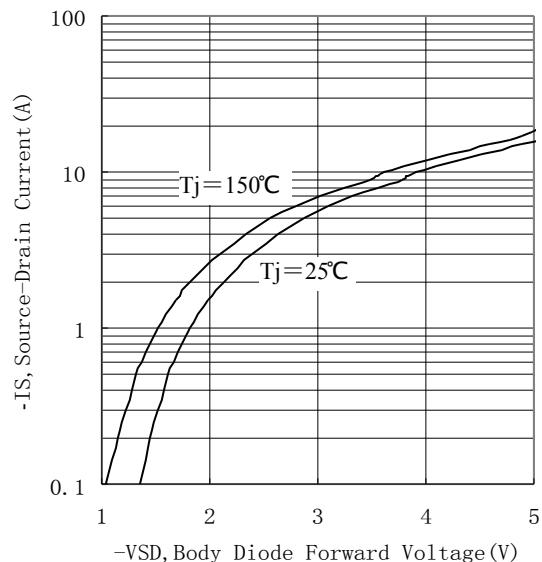


Figure 8 . Source-Drain Diode Forward

Package Outline Dimensions (UNIT: mm)

SOT-23

